

N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) |
|--------------|----------------------------|-----------|
| 100 | 0.0075 at $V_{GS} = 10$ V | 85 |
| | 0.0095 at $V_{GS} = 4.5$ V | 75 |

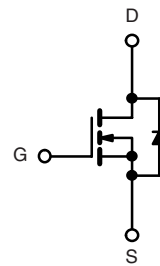
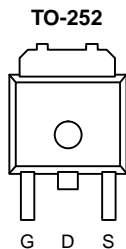
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested


RoHS
 COMPLIANT

APPLICATIONS

- Primary Side Switch
- Isolated DC/DC Converter



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

| Parameter | Symbol | Limit | Unit |
|--|----------------|-----------------|------------------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current ($T_J = 150^\circ\text{C}$) | I_D | 85 | A |
| | | 75 ^a | |
| Pulsed Drain Current | I_{DM} | 300 | |
| Avalanche Current | I_{AS} | 75 | mJ |
| Single Pulse Avalanche Energy ^b | E_{AS} | 280 | |
| Maximum Power Dissipation ^b | P_D | 210 | W |
| | | 3.25 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 175 | $^\circ\text{C}$ |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Typical | Maximum | Unit |
|--|------------|---------|---------|--------------------|
| Maximum Junction-to-Ambient ^b | R_{thJA} | 40 | 50 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Case | R_{thJC} | 0.85 | 1.1 | |

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

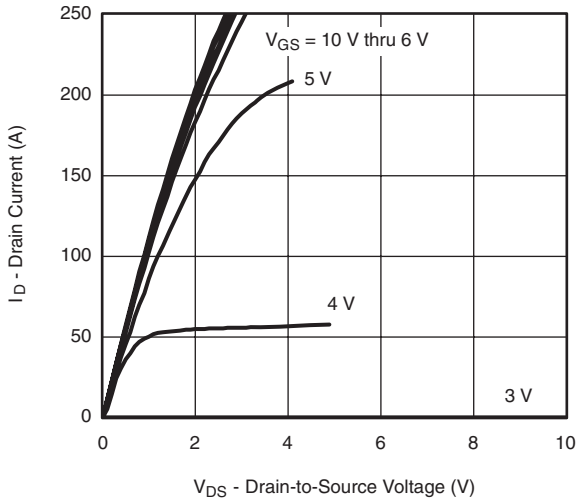
| SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted | | | | | | |
|--|---------------|--|------|--------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 100 | | | V |
| Gate-Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 1 | | 3 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^{\circ}\text{C}$ | | | 50 | |
| | | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^{\circ}\text{C}$ | | | 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} = \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | 120 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}$ | | 0.0075 | 0.010 | Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$ | | 0.0095 | 0.012 | |
| | | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$ | | | 0.017 | |
| | | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$ | | | 0.022 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 30\text{ A}$ | 25 | | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 4550 | | pF |
| Output Capacitance | C_{oss} | | | 565 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 205 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$ | | 105 | 160 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 17 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 23 | | |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 50\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$ | | 12 | 25 | ns |
| Rise Time ^c | t_r | | | 90 | 135 | |
| Turn-Off DelayTime ^c | $t_{d(off)}$ | | | 55 | 85 | |
| Fall Time ^c | t_f | | | 130 | 195 | |
| Source-Drain Diode Ratings and Characteristics $T_C = 25\text{ }^{\circ}\text{C}$ ^b | | | | | | |
| Continuous Current | I_S | | | | 85 | A |
| Pulsed Current | I_{SM} | | | | 240 | |
| Forward Voltage ^a | V_{SD} | $I_F = 85\text{ A}, V_{GS} = 0\text{ V}$ | | 1.0 | 1.5 | V |
| Reverse Recovery Time | t_{rr} | $I_F = 50\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$ | | 85 | 140 | ns |
| Peak Reverse Recovery Current | $I_{RM(REC)}$ | | | 4.5 | 7 | A |
| Reverse Recovery Charge | Q_{rr} | | | 0.17 | 0.35 | μC |

Notes:

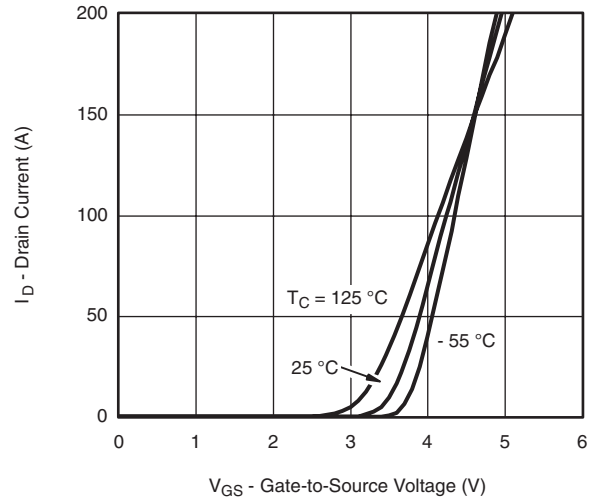
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

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TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted



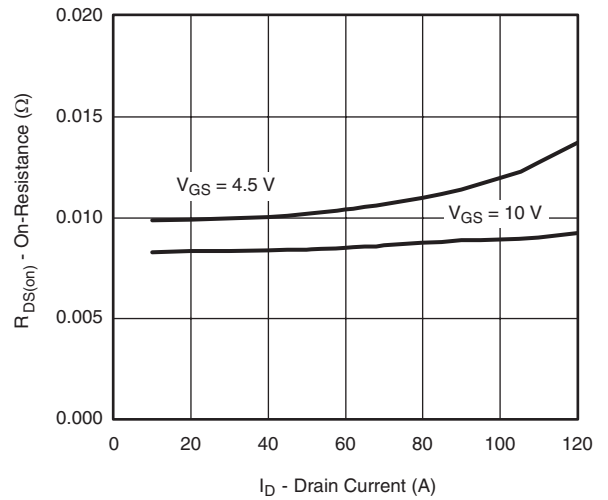
Output Characteristics



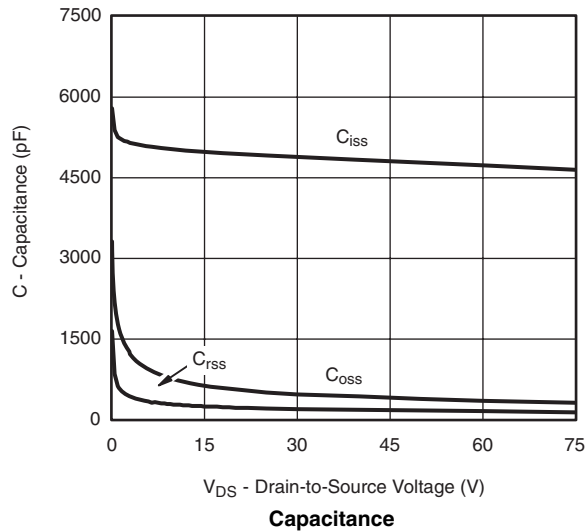
Transfer Characteristics



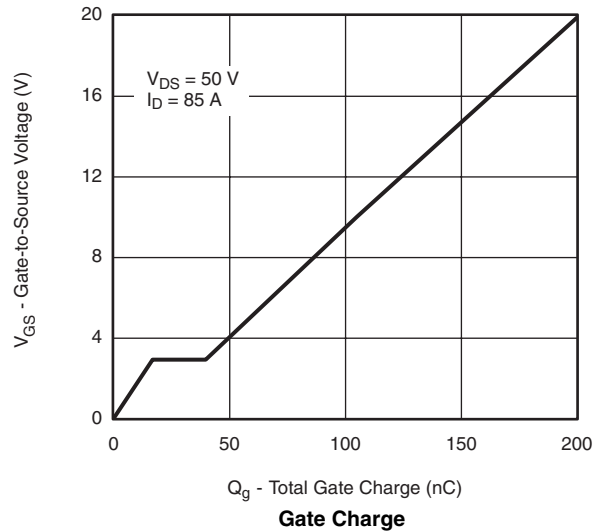
Transconductance



On-Resistance vs. Drain Current

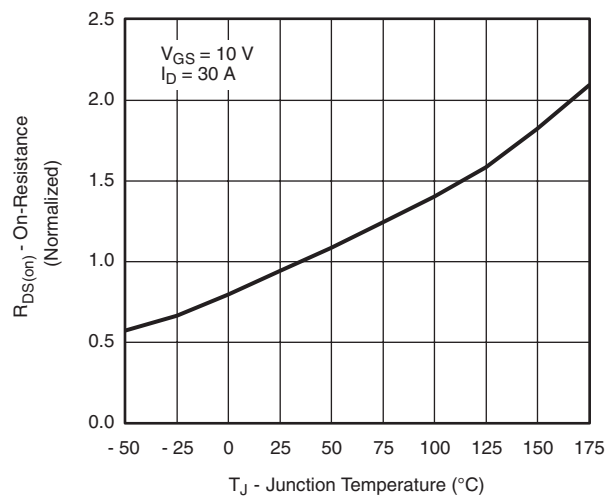


Capacitance

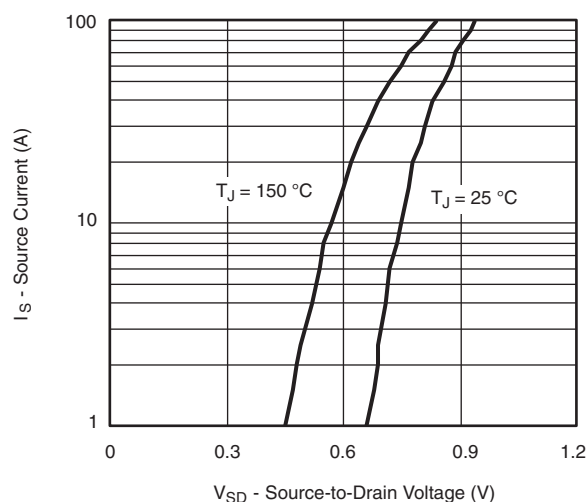


Gate Charge

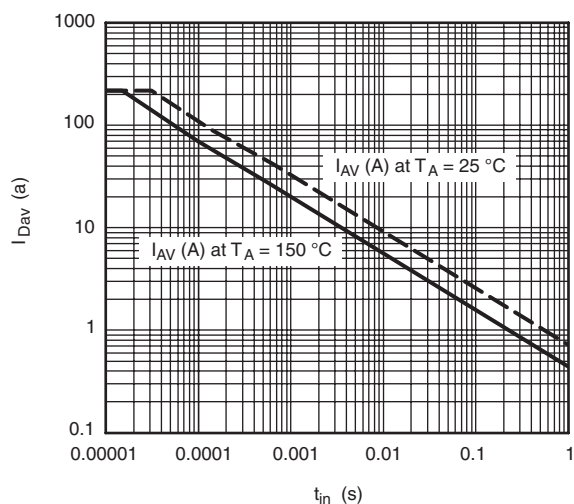
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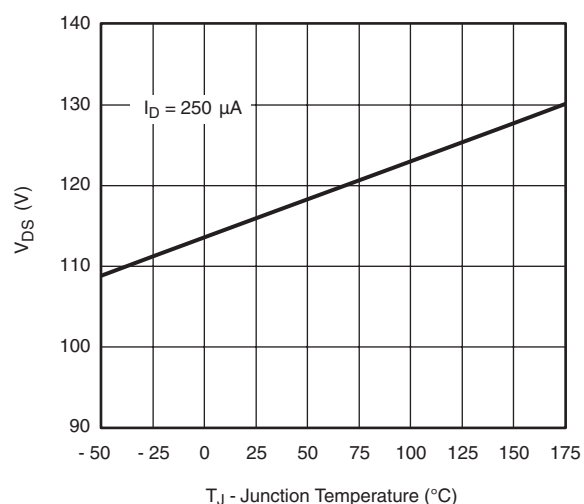
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

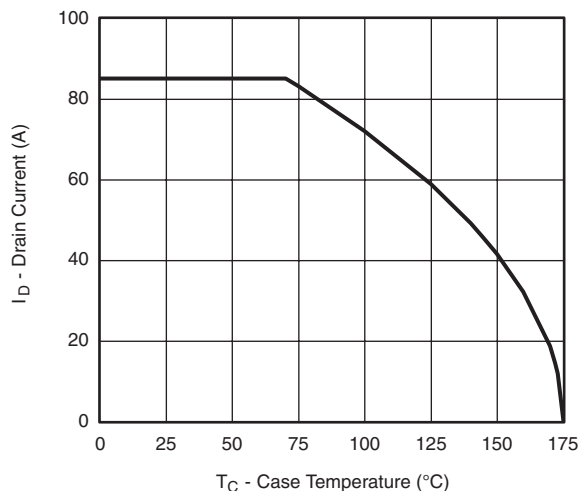


Avalanche Current vs. Time

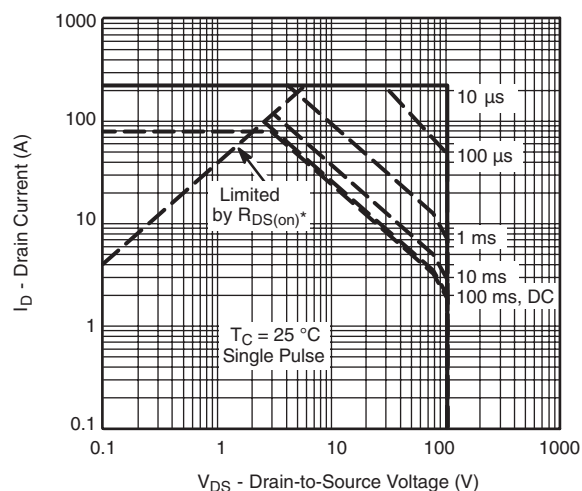


T_J - Drain-Source Breakdown vs. Junction-Temperature

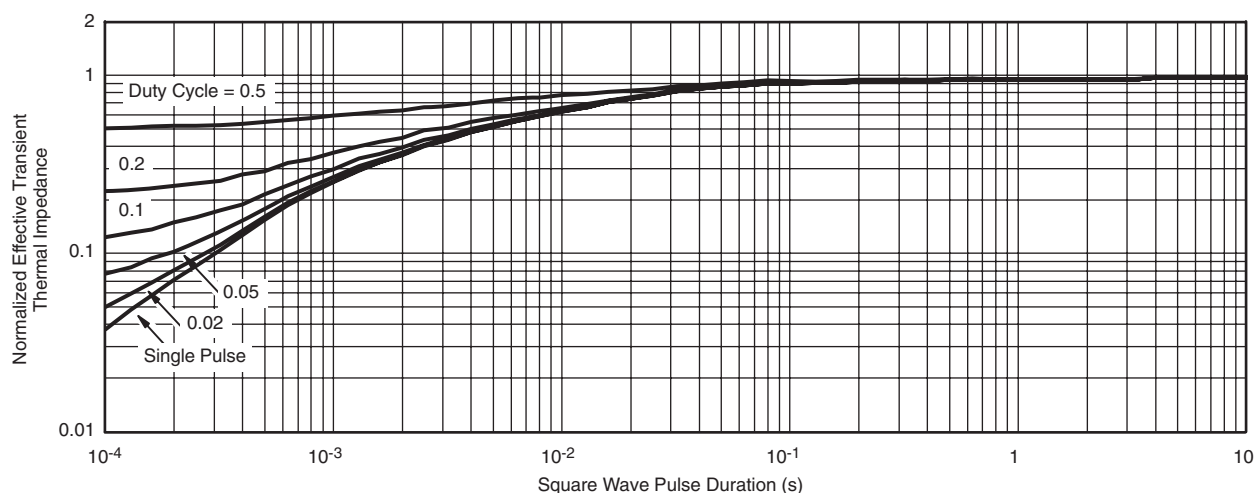
THERMAL RATINGS



**Maximum Avalanche and Drain Current
vs. Case Temperature**

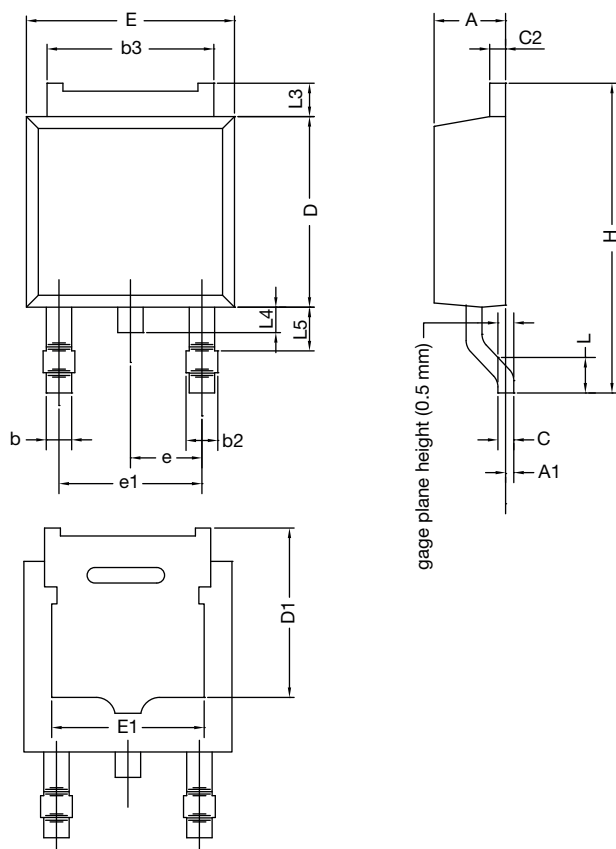


Safe Operating Area
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252AA CASE OUTLINE

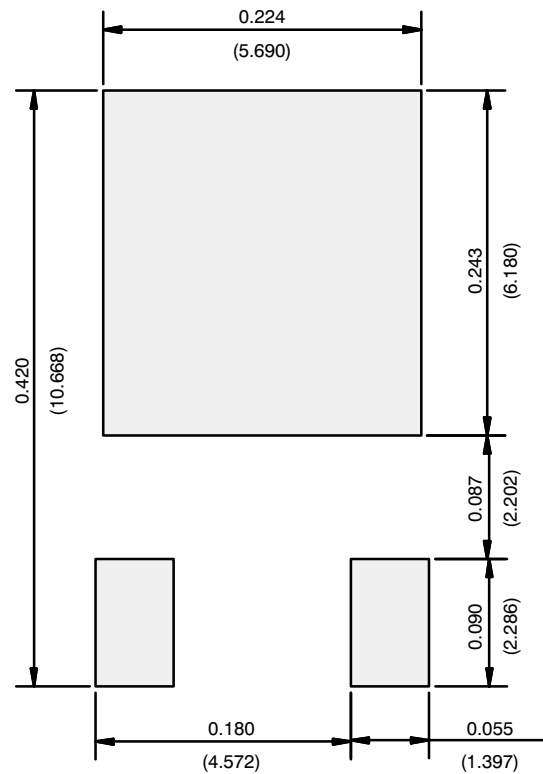


| DIM. | MILLIMETERS | | INCHES | |
|---------------------------------|-------------|-------|-----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 2.18 | 2.38 | 0.086 | 0.094 |
| A1 | - | 0.127 | - | 0.005 |
| b | 0.64 | 0.88 | 0.025 | 0.035 |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 |
| C | 0.46 | 0.61 | 0.018 | 0.024 |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 5.21 | - | 0.205 | - |
| E | 6.35 | 6.73 | 0.250 | 0.265 |
| E1 | 4.32 | - | 0.170 | - |
| H | 9.40 | 10.41 | 0.370 | 0.410 |
| e | 2.28 BSC | | 0.090 BSC | |
| e1 | 4.56 BSC | | 0.180 BSC | |
| L | 1.40 | 1.78 | 0.055 | 0.070 |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 |
| L4 | - | 1.02 | - | 0.040 |
| L5 | 1.14 | 1.52 | 0.045 | 0.060 |
| ECN: X12-0247-Rev. M, 24-Dec-12 | | | | |
| DWG: 5347 | | | | |

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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